

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Kiyoshi TBNIO

Serial No.: 09/428,052

Filed: October 27, 1999

Group Art Unit: 2815

Examiner: J. Diaz

For: METHOD OF FABRICATING A SEMICONDUCTOR DEVICE CONTAINING
NITROGEN IN A GATE OXIDE FILM (AS AMENDED)



Amdt
11/D
6-6-01

T. Flores

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Date: May 24, 2001

Sir:

In response to the Office Action dated January 26, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 8 and 9 without prejudice or disclaimer.

Please amend claims 6, 10 and 13 as follows:

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6. (Twice Amended) A method of fabricating a semiconductor device, comprising the steps

of:

forming a gate oxide film on a substrate;

forming a gate electrode pattern on said gate oxide film; and

Sub
EA
of:

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